

**General Description**

It combines advanced trench MOSFET technology with a low resistance package to provide extremely

Ordering Information:**Absolute Maximum Ratings $T_c = 25$**

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	120	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25}$	80	A
	$I_{D@TC=75}$	60	A
	$I_{D@TC=100}$	50	A
Pulsed Drain Current	I_{DM}	240	A
Total Power Dissipation($TC=25$)	$P_D@TC=25$	125	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy@L=0.1mH	E_{AS}	80	mJ
Avalanche Current@L=0.1mH	I_{AS}	40	A

**Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	1.0	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	50	° C/W
Soldering temperature, wavesoldering for 10s	T				



				56		nS
				38		nC

Note: 1 1% ;

Fig.1 Gate-Charge Characteristics

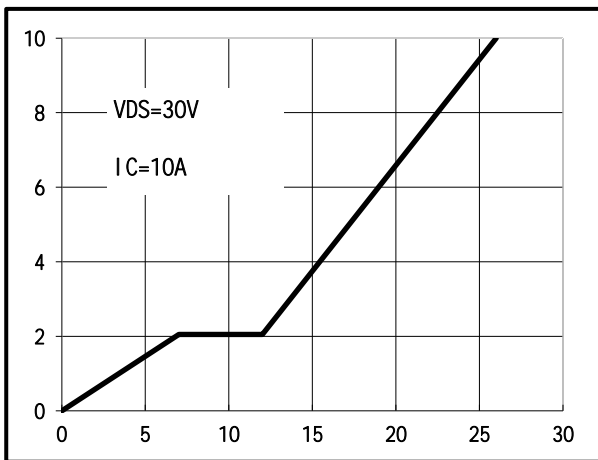


Fig.2 Capacitance Characteristics

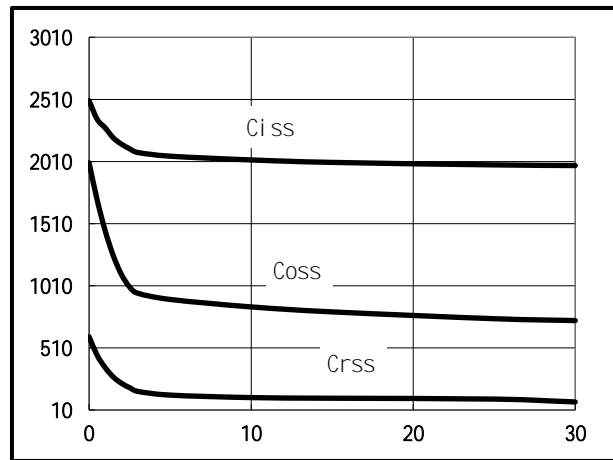


Fig.3 Power Dissipation

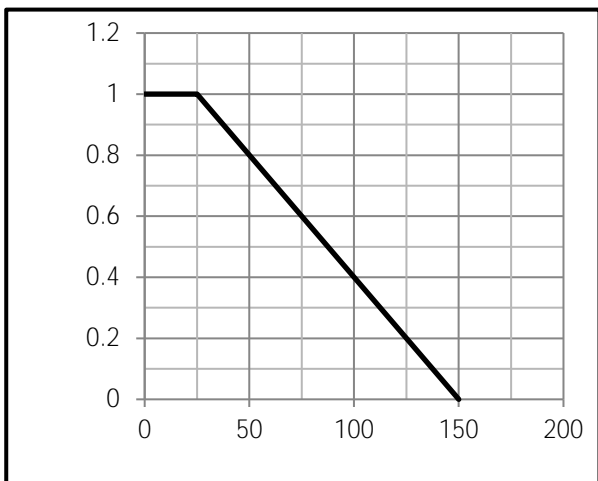


Fig.4 Typical output Characteristics

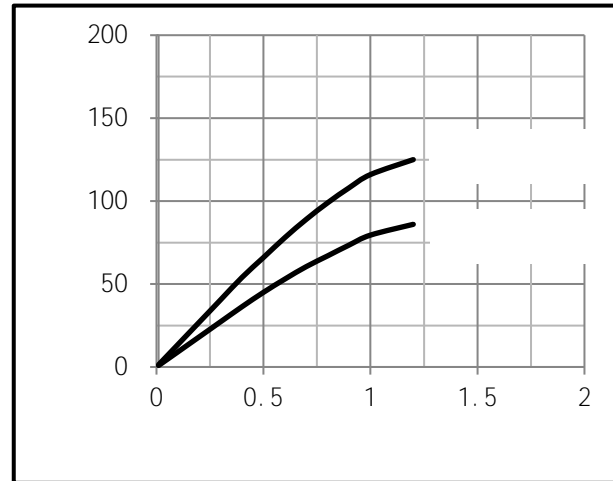




Fig.5 Threshold Voltage V.S Junction Temperature

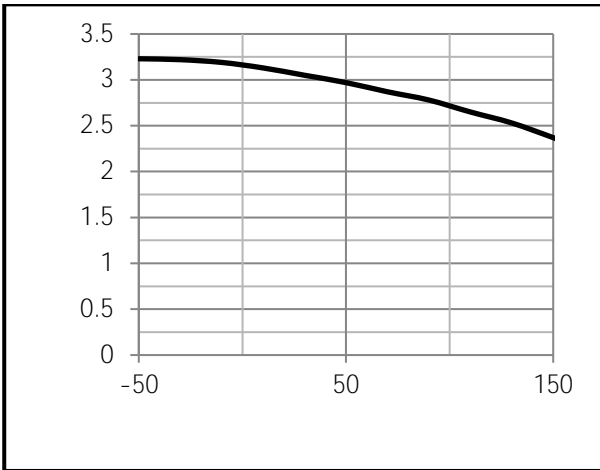


Fig.6 Resistance V.S Drain Current

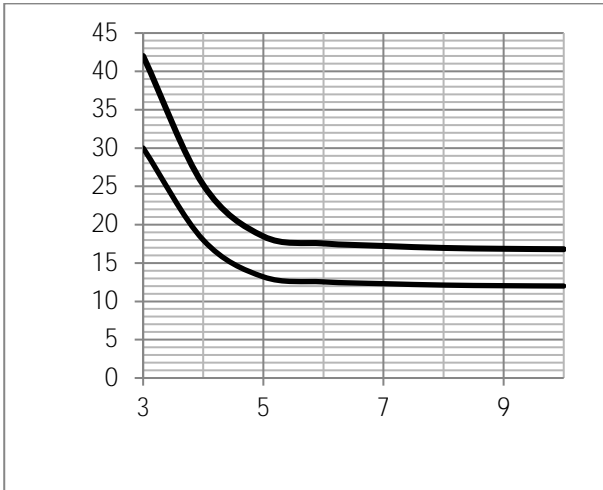
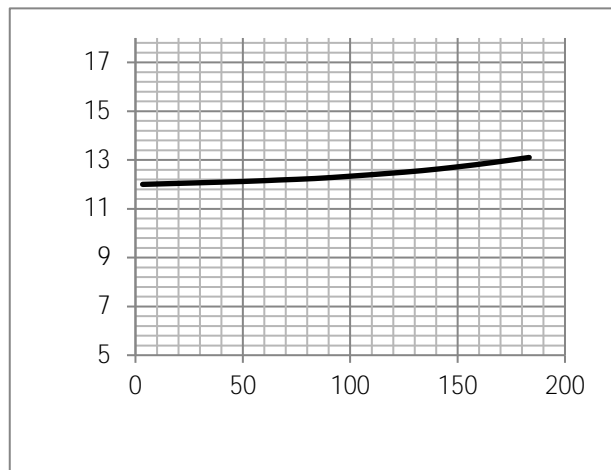


Fig.9 Switching Time Measurement Circuit

Fig.10 Gate Charge Waveform





Fig.11 Switching Time Measurement Circuit

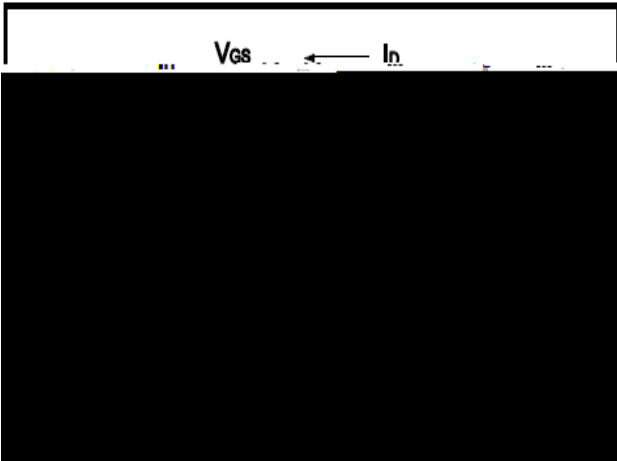


Fig.12 Gate Charge Waveform

